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# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										外形	備考
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>FE</sub> h <sub>FE</sub> * (Ω)	h <sub>FE</sub> h <sub>FE</sub> * (×10 <sup>-4</sup> )	h <sub>FE</sub> h <sub>FE</sub> * (μS)	f <sub>αb</sub> f <sub>r</sub> * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
  - 9 f<sub>αb</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>r</sub>.
  - 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
  - 11 OUTLINE
  - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)										外形	備考							
				V <sub>CB0</sub> (V)	V <sub>EB0</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>CB0</sub> 最大値 (μA)	V <sub>CB(V)</sub>	直流又はパルス V <sub>CE(V)</sub>	h <sub>FE</sub> I <sub>C(mA)</sub>	バイアス V <sub>CB(V)</sub>	I <sub>E(mA)</sub>	h <sub>fe</sub> h <sub>jb</sub> *	h <sub>ie</sub> h <sub>ib</sub> * (Ω)	h <sub>re</sub> h <sub>rb</sub> * (×10 <sup>-4</sup> )	h <sub>rs</sub> h <sub>rb</sub> * (μU)			f <sub>β</sub> f <sub>T</sub> * (Mc)	C <sub>ob</sub> (pF)	τ <sub>bb</sub> h <sub>ie(ideal)</sub> * (ns)	τ <sub>bb</sub> C <sub>c</sub> τ <sub>bb</sub> * (ns)			
2SC1601	新日無	RF.AF.LN	Si.EP	35		100	200	175	0.05	20	150	6	1	6	-0.1	NP=2dB (f=1kHz)		50k	5	15	200*	2	C <sub>c</sub> τ <sub>bb</sub> * 60pS	243			
" 1602	"	RF.AF	"	35		100	150	125	0.05	20	150	6	1	6	-0.1			50k	5	15	200*	2	C <sub>c</sub> τ <sub>bb</sub> * 60pS	27			
" 1603	三菱	PA	"	18	4	600	6W (T <sub>c</sub> =25°C)	175	100	10	50	7	100			P <sub>0</sub> =1.5W (f=485MHz, V <sub>cc</sub> =7.2V, P <sub>i</sub> =0.3W)									312		
" 1604	"	"	"	18	4	300	5W (T <sub>c</sub> =25°C)	175	30	10	40	7	50			P <sub>0</sub> =0.35W (f=485MHz, V <sub>cc</sub> =7.2V, P <sub>i</sub> =50mW)									255		
" 1605	"	"	"	35	4.5	3.5A	30W (T <sub>c</sub> =25°C)	175	500	25	50	10	100			P <sub>0</sub> =16W (f=175MHz, V <sub>cc</sub> =13.5V, P <sub>i</sub> =1.7W)									113		
" 1606	"	PA	"	40	4	600	6W (T <sub>c</sub> =25°C)	175	100	25	50	10	100			P <sub>0</sub> =3W (f=175MHz, V <sub>cc</sub> =13.5V, P <sub>i</sub> =0.2W)									271		
" 1607	富士通	RF	Si.EP	40	3.5	100	180	175	100	20	50	5	50	12.5	-10	G <sub>pε</sub> =12dB (f=200MHz)						4		50C			
" 1608	"	PA	"	40	3.5	500	5W (T <sub>c</sub> =25°C)	175	100	20	50	5	200			P <sub>0</sub> =1.6W (f=470MHz, V <sub>cc</sub> =12.5V, P <sub>i</sub> =0.3W)						5		231			
" 1609	日電	SW	Si.EMe	140	6	25A	120W (T <sub>c</sub> =25°C)	175	10	140	30	2	13A			t <sub>on</sub> <0.5μS, t <sub>off</sub> <2μS t <sub>rise</sub> <1.5μS									102		
" 1610	"	"	"	150	7	10A	100W (T <sub>c</sub> =25°C)	175	100	100	60	5	5A			t <sub>on</sub> <0.5μS, t <sub>off</sub> <2μS t <sub>rise</sub> <1.5μS									102		
" 1611																											
" 1612																											
" 1613	東洋電具	SW	Si.TP	130	5	30	150	125	1	80	56-270	3	5	5	-2							60*	6		235		
" 1614	"	"	"	180	5	30	150	125	1	120	56-270	3	5	5	-2							60*	6		235		
" 1615	"	"	"	210	5	30	150	125	1	150	56-270	3	5	5	-2							60*	6		235		
" 1616																											
" 1617	東芝	PA	Si.T	300	5	7A	50W (T <sub>c</sub> =25°C)	150	1mA	250	30-150	5	1A	5	-500							10*	100		102	水平偏向用	
" 1618	サンケン	"	Si.TMe	80	6	6A	50W (T <sub>c</sub> =25°C)	150	1mA	80	60	4	3A	12	-500							10*	85	12*	102	2SA807 とコンプアリ	
" 1619	"	"	"	100	6	6A	50W (T <sub>c</sub> =25°C)	150	1mA	100	60	4	3A	12	-500							10*	85	12*	102	2SA808 とコンプアリ	
" 1620	松下	PA	Si.EP	36	3	600	10W (T <sub>c</sub> =25°C)	175	100	15	50	13.5	100	13.5	-150	P <sub>0</sub> =2.6W, G <sub>pε</sub> =6.34dB (f=500MHz, V <sub>cc</sub> =13.5V, P <sub>i</sub> =0.6W)					1200*	7		227			
" 1621	日電	SW	Si.E	25	5	200	150	125	0.1	15	85	0.5	1	10	-10	t <sub>on</sub> <20μS, t <sub>off</sub> <40μS t <sub>rise</sub> <20μS						400*	<6		176		
" 1622	"	RF.AF	"	40	5	100	150	125	0.05	25	500	3	0.5	6	-1							100*	3.5	50	176		
" 1623	"	"	"	60	5	100	150	125	0.1	60	200	6	1	6	-10							250*	3	25*	176		
" 1624	東芝	PA	Si.P	120	5	1A	15W (T <sub>c</sub> =25°C)	150	1	50	70-240	5	150	5	-150								30*	20		268	2SA814 とコンプアリ
" 1625	"	"	"	100	5	1A	15W (T <sub>c</sub> =25°C)	150	1	50	70-240	5	150	5	-150								30*	20		268	2SA815 とコンプアリ
" 1626	"	"	Si.E	80	5	750	15W (T <sub>c</sub> =25°C)	150	0.5	30	70-240	2	150	2	-150								100*	15		268	2SA816 とコンプアリ
" 1627	"	"	"	80	5	300	600	150	0.1	50	70-240	2	50	2	-50								150*	6		138	2SA817 とコンプアリ
" 1628	"	"	Si.T	180	5	50	1W	150	1	100	70-240	5	10	10	-10								120*	<5		249	2SA818 とコンプアリ
" 1629	サンケン	PA	Si.TMe	90	6	6A	50W (T <sub>c</sub> =25°C)	150	1mA	90	1000	4	1A	12	-500								10*	95	80*	102	
" 1630	ソニー	RF	Si.E PaMe	175	5	30	750	175	1	25	100	5	3	10	-2	A <sub>β</sub>   = 1dB (f=100MHz)						3	C <sub>c</sub> τ <sub>bb</sub> * 40pS	181			